TOSHIBA Transistor Silicon NPN Epitaxial Type

# 2SC5376FV

Audio Frequency General Purpose Amplifier Applications For Muting and Switching Applications

Low Collector Saturation Voltage:  $V_{CE (sat) (1)} = 15 \text{ mV (typ.)}$ 

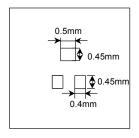
 $@I_C = 10 \text{ mA/I}_B = 0.5 \text{ mA}$ 

High Collector Current: I<sub>C</sub> = 400 mA (max)

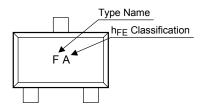
#### Maximum Ratings (Ta = 25°C)

| Characteristics             | Symbol           | Rating  | Unit |
|-----------------------------|------------------|---------|------|
| Collector-base voltage      | $V_{CBO}$        | 15      | V    |
| Collector-emitter voltage   | V <sub>CEO</sub> | 12      | V    |
| Emitter-base voltage        | V <sub>EBO</sub> | 5       | V    |
| Collector current           | Ic               | 400     | mA   |
| Base current                | lΒ               | 50      | mA   |
| Collector power dissipation | PC               | 150 *   | mW   |
| Junction temperature        | Tj               | 150     | °C   |
| Storage temperature range   | T <sub>stg</sub> | -55~150 | °C   |

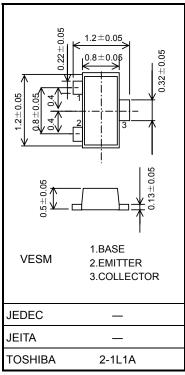
<sup>\* :</sup> Mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6mmt)



### Marking



Unit: mm



Weight: 0.0015g (typ.)

## Electrical Characteristics (Ta = 25°C)

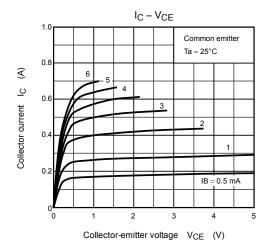
| Character                            | istics       | Symbol                    | Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------------|--------------|---------------------------|---|-----|------|------|------|
| Collector cut-off current            | t            | I <sub>CBO</sub>          | $V_{CB} = 15 \text{ V}, I_{E} = 0$  | _   | _    | 0.1  | μΑ   |
| Emitter cut-off current              |              | I <sub>EBO</sub>          | $V_{EB} = 5 \text{ V}, I_{C} = 0$   | _   | _    | 0.1  | μΑ   |
| DC current gain                      |              | h <sub>FE</sub> (Note)    | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 10 mA   | 300 | _    | 1000 |      |
| Collector-emitter saturation voltage |              | V <sub>CE</sub> (sat) (1) | $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$   | _   | 15   | 30   | mV   |
|                                      |              | V <sub>CE</sub> (sat) (2) | $I_C = 200 \text{ mA}, I_B = 10 \text{ mA}$   | _   | 110  | 250  | mV   |
| Base-emitter voltage                 |              | V <sub>BE (sat)</sub>     | $I_C = 200 \text{ mA}, I_B = 10 \text{ mA}$   | _   | 0.87 | 1.2  | V    |
| Transition frequency                 |              | f <sub>T</sub>            | $V_{CE} = 2 V$ , $I_C = 10 \text{ mA}$  | 80  | 130  | _    | MHz  |
| Collector output capacitance         |              | C <sub>ob</sub>           | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz   | _   | 4.2  | _    | pF   |
| Collector-emitter on resistance      |              | Ron                       | $I_B = 1 \text{ mA}, V_{in} = 1 V_{rms}, f = 1 \text{ kHz}$   | _   | 0.9  | _    | Ω    |
| Switching time                       | Turn-on time | t <sub>on</sub>           | OUTPUT $\begin{array}{c c} & & & & & & \\ 0 \ V & & & & & \\ \hline 10 \ \mu S & & & & & \\ \hline & & & & & \\ \hline & & & & & \\ \hline & & & &$ | _   | 85   | _    | ns   |
|                                      | Storage time | t <sub>stg</sub>          |   | _   | 170  | _    | ns   |
|                                      | FallI time   | t <sub>f</sub>            |   | _   | 40   | _    | ns   |

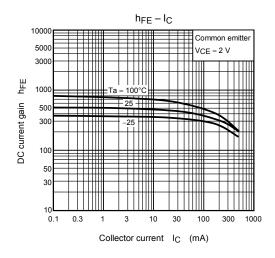
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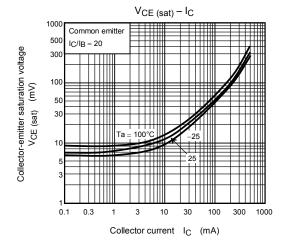
Note: hFE Classification

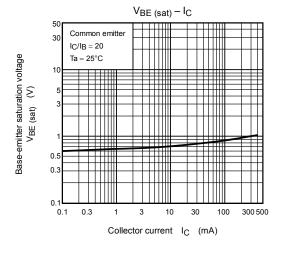
A: 300 ~ 600, B: 500 ~ 1000

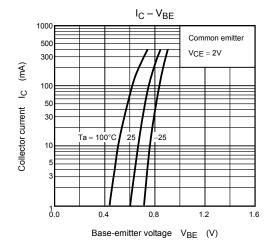
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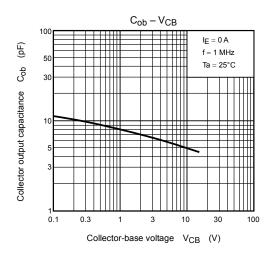




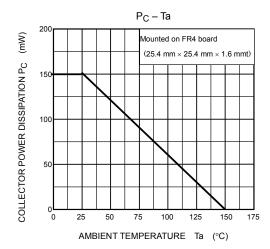








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